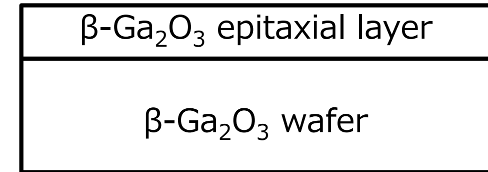
Standard specifications of Φ4 inch HVPE β-Ga_2O_3 epitaxial wafer

Epitaxial layer (Growth method: HVPE)

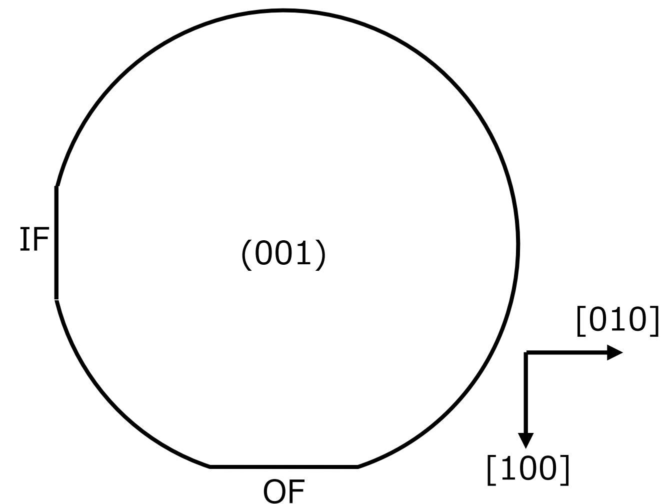
Property	Specification
Dopant	Si (n-type)
Doping concentration	$2x10^{16}$ cm^{-3}
Thickness	Specify a value in the range between 5 and 10 μm



Cross section of β-Ga_2O_3 epitaxial wafer

Wafer

Property	Specification
Dopant	Sn (n-type)
Doping concentration	$1x10^{18}$~$2x10^{19}$ cm^{-3}
Orientation	(001)
Size	Φ4 inch
Thickness	0.65 mm
XRD FWHM	≦350 arcsec
Off set angle	0°±1°



Orientation

Remarks
1 These products must be used for research and development purposes only.
2 The substrates must not be used as a seed crystal.
3 The specifications are subject to change without notice.

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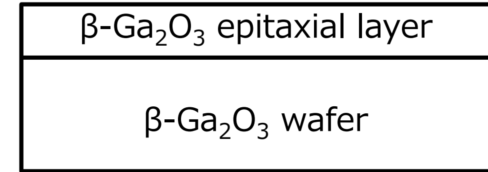
Standard specifications of Φ2 inch HVPE $\beta\text{-}Ga_2O_3$ epitaxial wafer

Epitaxial layer (Growth method: HVPE)

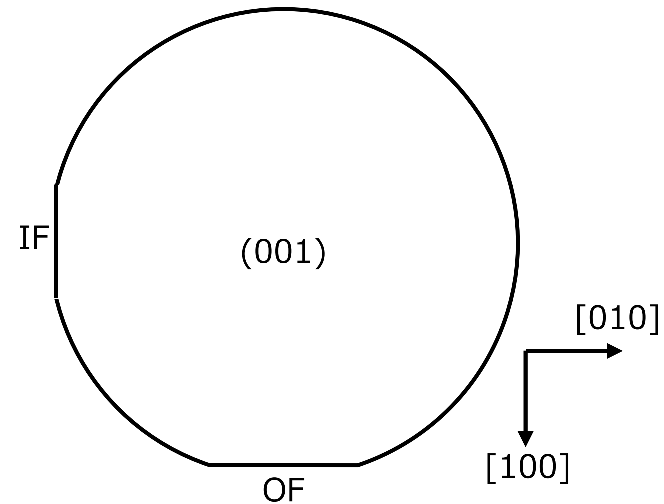
Property	Specification
Dopant	Si (n-type)
Doping concentration	Specify a value in the range between $2x10^{16}$ and $9x10^{16}$ cm^{-3}
Thickness	Specify a value in the range between 5 and 10 μm



Cross section of $\beta\text{-}Ga_2O_3$ epitaxial wafer

Wafer

Property	Specification
Dopant	Sn (n-type)
Doping concentration	$1x10^{18}$~$2x10^{19}$ cm^{-3}
Orientation	(001)
Size	Φ2 inch
Thickness	0.65 mm
XRD FWHM	≦350 arcsec
Off set angle	0°±1°



Orientation

Remarks
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